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# *Photocathode Studies for the Argonne Wakefield Accelerator RF Photoinjector*

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# OUTLINE

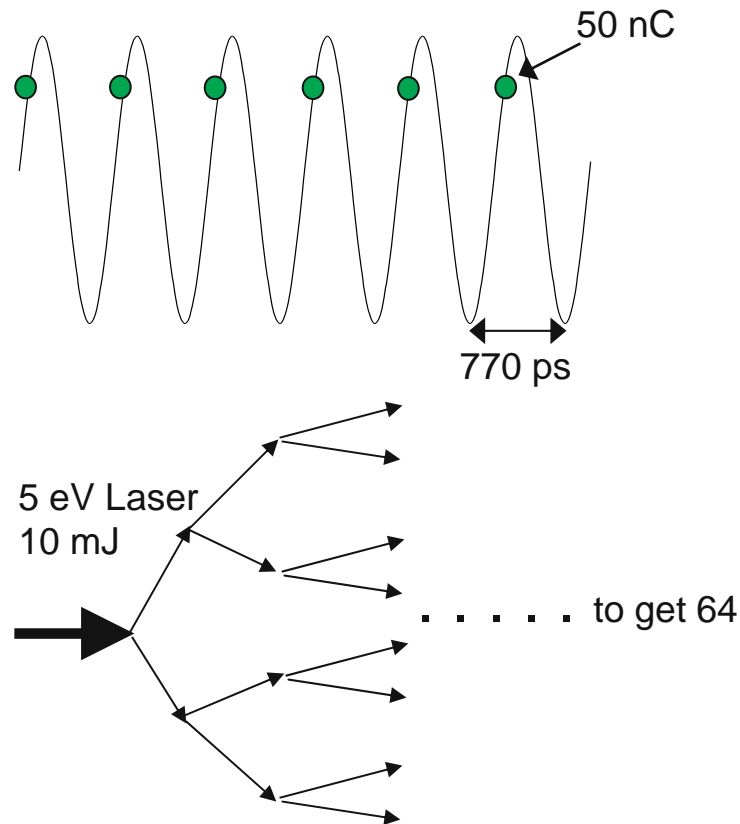
- Overview of photocathodes for photoinjectors;
- Photocathode requirement for the AWA;
- Status of high QE photocathode fabrication at the AWA;
- Schottky-enabled photoemission in photoinjectors;
- High-gradient/breakdown studies.

# OVERVIEW OF PHOTOCATHODES FOR PHOTOINJECTORS

PHOTOCATHODE	GOOD	BAD
<b>Metallic</b> <i>(Cu, Mg, Ag, etc.)</i>	<ul style="list-style-type: none"> <li>■ Easy to obtain/handle</li> <li>■ Still widely-used</li> <li>■ Does not require UHV</li> <li>■ QE remains constant for long period of time</li> <li>■ Fast response time (<math>\sim 10^{-15}</math>s)</li> <li>■ Low dark currents</li> </ul>	<ul style="list-style-type: none"> <li>■ Low QE (<math>\sim 10^{-4}</math>-<math>10^{-6}</math>)</li> </ul>
<b>Semiconductor</b> <i>(Cs<sub>2</sub>Te, K<sub>2</sub>Te, GaN, etc.)</i>	<ul style="list-style-type: none"> <li>■ High QE (0.05 – 0.3)</li> <li>■ Photoelectrons have lower energy spread (in principle) than metallic</li> </ul>	<ul style="list-style-type: none"> <li>■ Requires UHV</li> <li>■ Surface deteriorates with O<sub>2</sub></li> <li>■ Longer response time than metallic (<math>\sim 10^{-13}</math>s)</li> <li>■ Initial QE has short lifetime</li> </ul>
<b>Negative Electron Affinity</b> <i>(GaAs family, GaP, etc.)</i>	<ul style="list-style-type: none"> <li>■ Even higher QE than semiconductor (0.1 – 0.6)</li> <li>■ Widely used in PMT</li> <li>■ Possible source of polarized electrons (GaAs family)</li> </ul>	<ul style="list-style-type: none"> <li>■ Requires UHV</li> <li>■ Even longer response time than semiconductor (<math>\sim 10^{-9}</math>s)</li> <li>■ May have higher dark currents</li> </ul>
<b>Liquid Metal, Superconducting compatible</b> <i>(Nb, NbN, etc.)</i>	<ul style="list-style-type: none"> <li>■ Possible use in superconducting RF photoinjector</li> </ul>	<ul style="list-style-type: none"> <li>■ Very little is known in accelerator situation</li> <li>■ QE yet to be determined – probably same as metallic?</li> </ul>

# PHOTOCATHODE REQUIREMENT FOR THE AWA

Creation of charge bunch train up to a maximum of 64 bunches in a single RF pulse



Want 50 nC in each charge microbunch. This is equal to  $\sim 3 \times 10^{11}$  electrons.

- 10 mJ of laser energy per pulse;
- Estimate 80% loss due to beam splitter, mirrors, etc.;
- Beam is split into 64 micro pulses;
- Number of photons in each micro pulse is  $\sim 4 \times 10^{13}$ .

QE of photocathode to be able to supply that amount of charge:

$$QE = \frac{3 \times 10^{11}}{4 \times 10^{13}} \approx 0.007 \approx 1\%$$

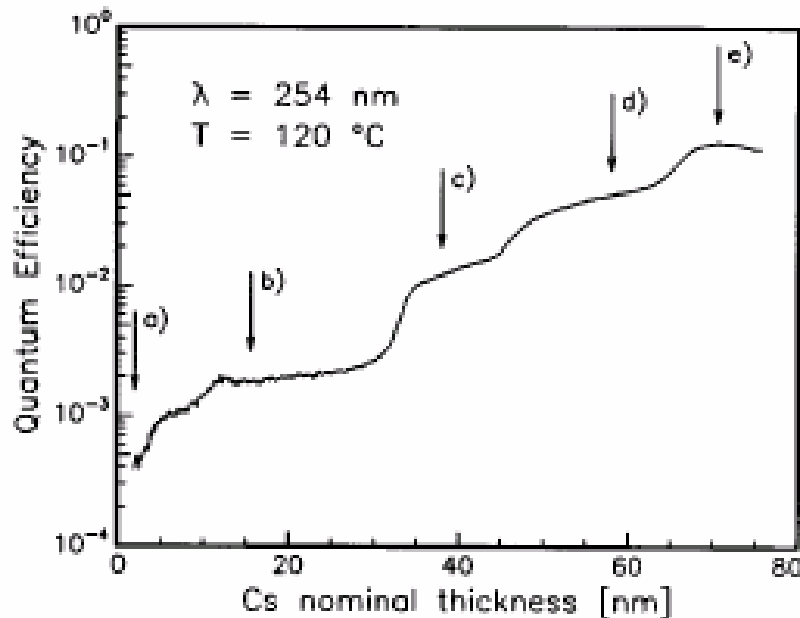
**Need high QE photocathode – choose  $\text{Cs}_2\text{Te}$**

# DEVELOPMENT OF $\text{Cs}_2\text{Te}$ PHOTOCATHODE 1

- High QE photocathode (maximum  $\sim 0.1$ - $0.3$  and lasts for  $\sim 1$ - $2$  days). QE then hovers around  $0.01$  for  $\sim 1$  month;
- A semiconductor with band gap of  $3.3$  eV and electron affinity of  $\sim 0.2$  eV. This translates to a “work function” of  $\sim 3.5$  eV;
- Requires vacuum at or better than  $10^{-9}$  Torr;
- Studies are continuing on (i) possible rejuvenation of QE and (ii) possible coating on surface to improve lifetime.

# DEVELOPMENT OF $Cs_2Te$ PHOTOCATHODE 2 – The Recipe

- Deposit 10-20 nm of Te on Mo substrate;
- Then deposit Cs and monitor QE using light source (typically  $h\nu \sim 5$  eV);
- Stop when QE reaches a peak.

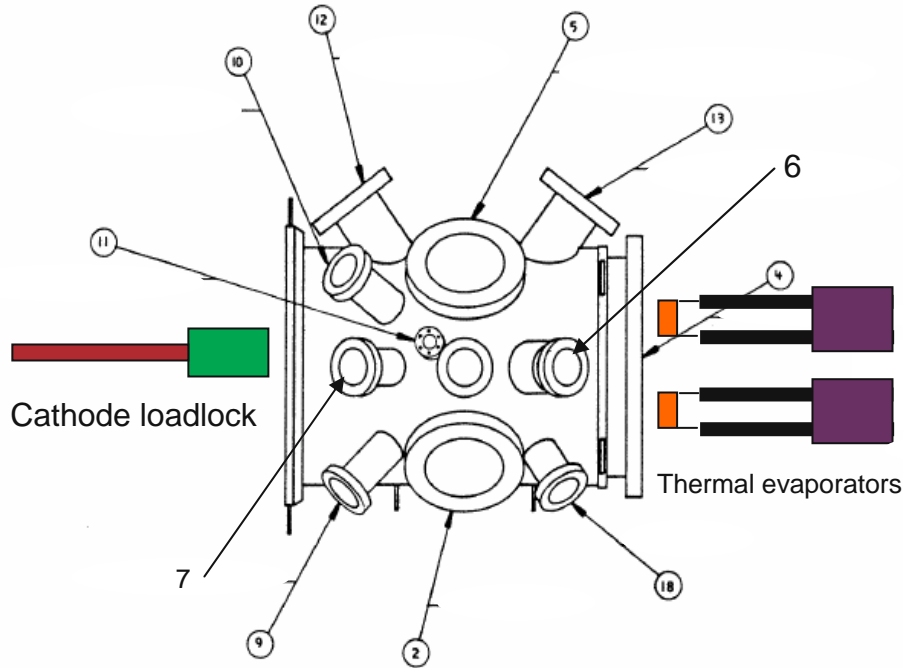


di Bona *et al.* J. Appl. Phys. **80**, 3024 (1996)

FIG. 1. Quantum efficiency as a function of the Cs nominal thickness during the fabrication of the photocathode. The substrate temperature is held at 120 °C. The arrows indicate the fabrication steps at which XPS experiments have been performed.

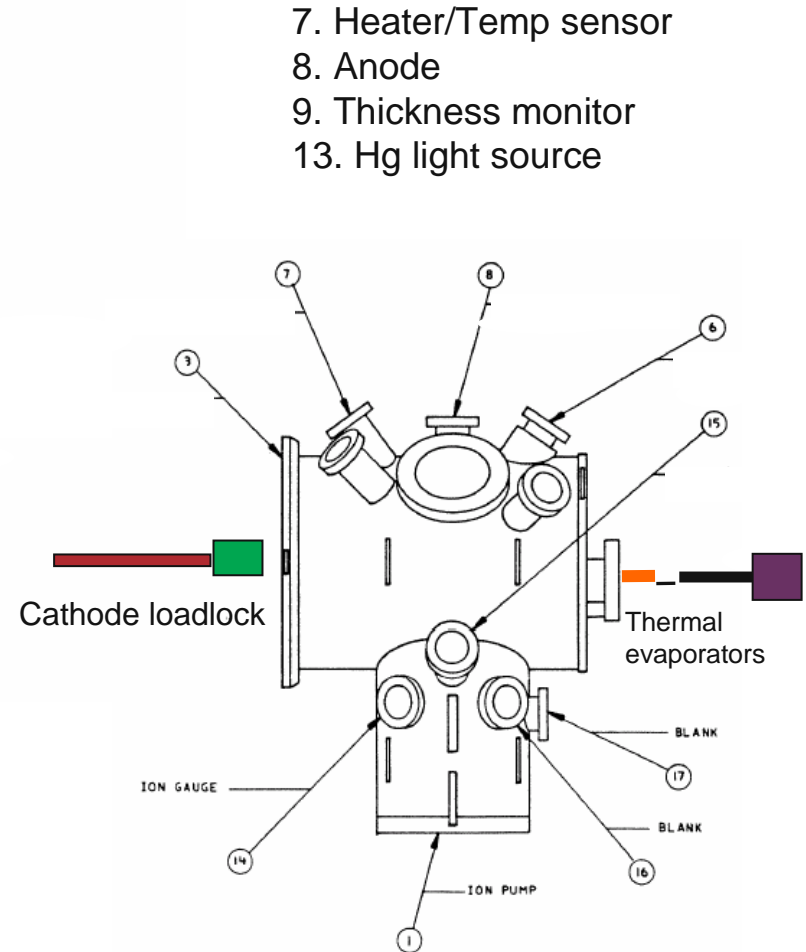
# DEVELOPMENT OF $Cs_2Te$ PHOTOCATHODE 3 – Deposition Facility

## SYSTEM TOP VIEW



- 7. Heater/Temp sensor
- 8. Anode
- 9. Thickness monitor
- 13. Hg light source

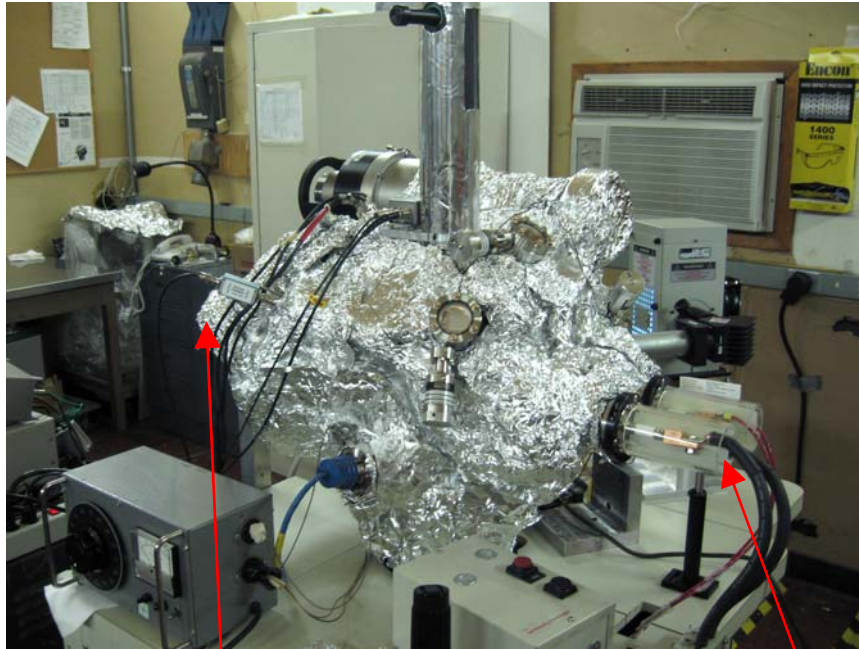
## SYSTEM SIDE VIEW



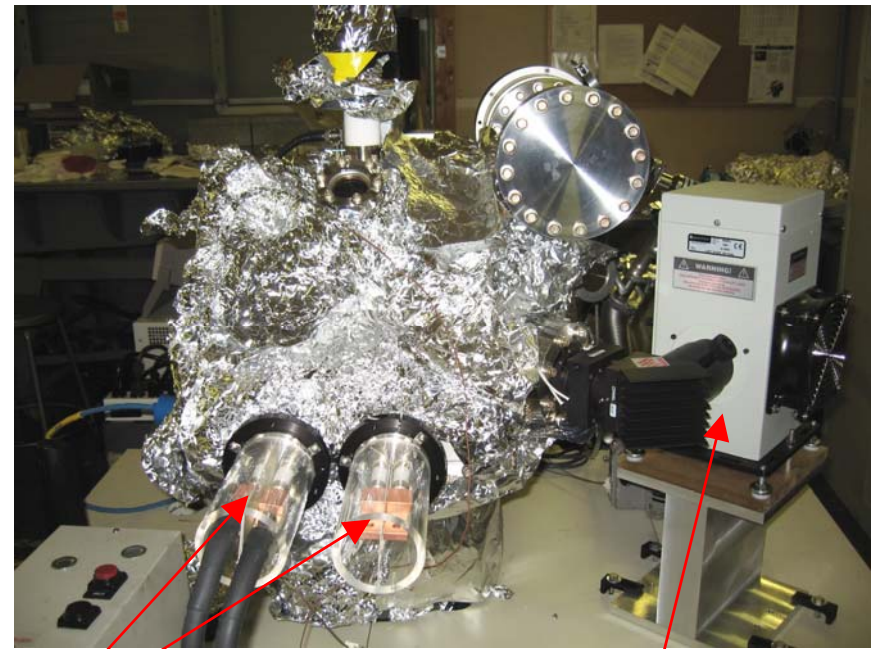
- 7. Heater/Temp sensor
- 8. Anode
- 9. Thickness monitor
- 13. Hg light source



# DEVELOPMENT OF $Cs_2Te$ PHOTOCATHODE 4 – Deposition Facility (cont)



Cathode load-lock transfer will be connected at this end



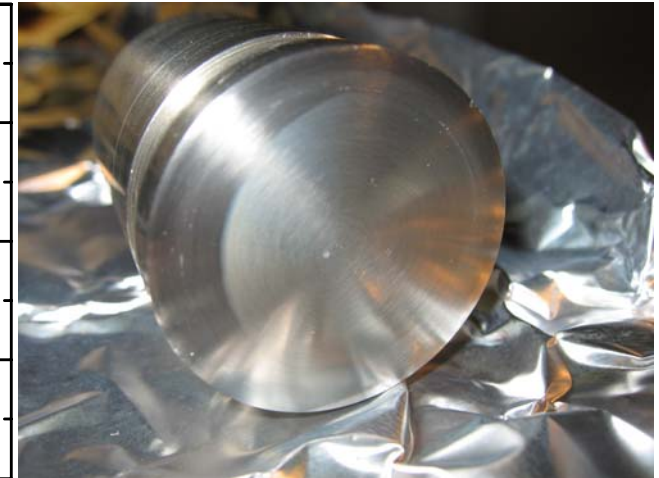
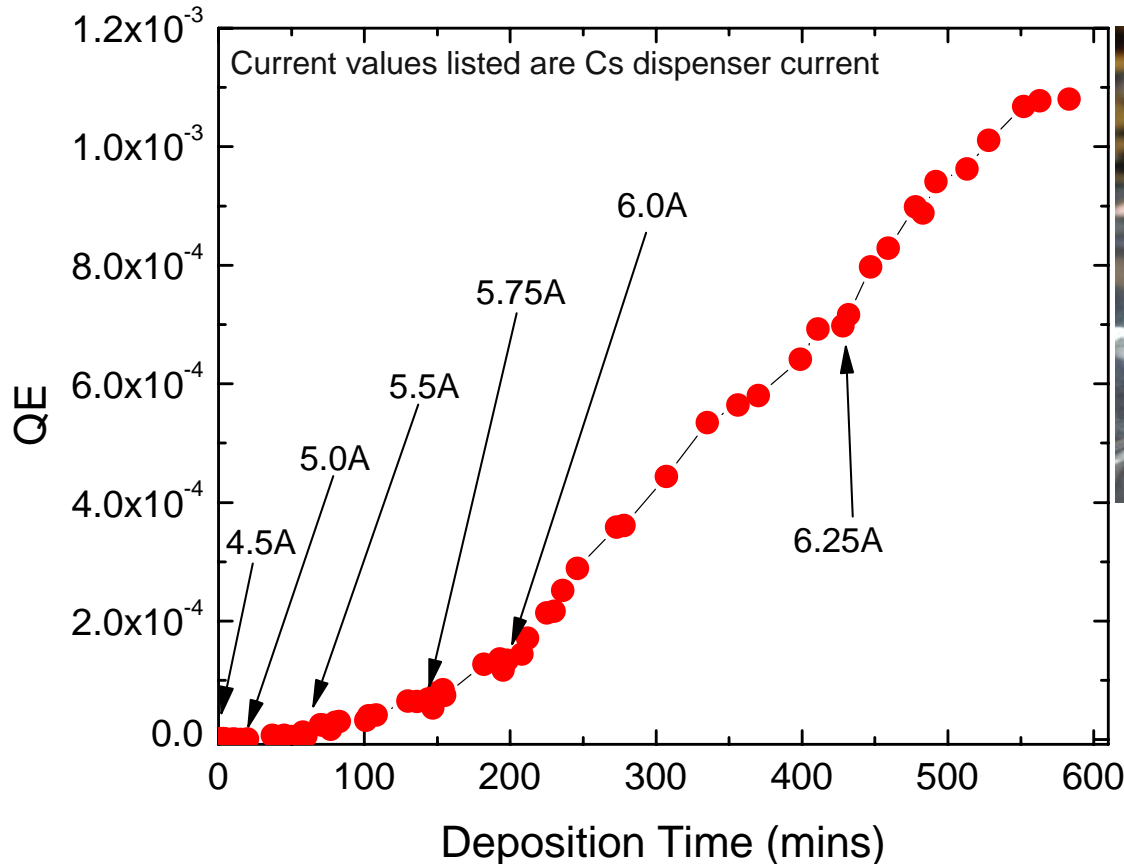
Thermal evaporators

Hg lamp



# DEVELOPMENT OF $Cs_2Te$ PHOTOCATHODE 5 – Our Progress So Far

## Cs Deposition on Te



We are ~2 orders of magnitude lower than expected. A few modifications will be made to the deposition chamber configurations.

# SCHOTTKY-ENABLED PHOTOEMISSION 1

Yusof *et al.*, Phys. Rev. Lett. **93**, 114801 (2004)

*“... it now appears that the intrinsic cathode emittance will be the dominant quantity that limits our achieving beams of higher brightness from an rf gun.”*

*ANL Theory Institute Workshop on Production of Bright Electron Beams  
Sept. 22-26, 2003*

- Study a new regime of electron beam generation that has potential impact on the future Linear Collider and Light sources;
- High brightness electron beam – minimize emittance;
- Scheme: Employ Schottky effect in the RF photocathode gun and with low energy photons;
- This technique also produces a reasonable estimate of the field enhancement factor without employing the Fowler-Nordheim model.

**In this presentation, thermal emittance = intrinsic emittance**

## SCHOTTKY-ENABLED PHOTOEMISSION 2 – Emittance in RF Photoinjector

Emittance from RF photocathode {KJ Kim, NIM **A275**, 1989}

$$\mathcal{E}^2 = \mathcal{E}_{thermal}^2 + \mathcal{E}_{RF}^2 + \mathcal{E}_{sc}^2 + 2 \mathcal{E}_{RF} \mathcal{E}_{sc} J_x$$

where  $\mathcal{E}_{RF}$  and  $\mathcal{E}_{sc}$  are the emittances from RF field in the gun and from space charge effect, respectively.  $J_x$  is correlation between  $\mathcal{E}_{RF}$  and  $\mathcal{E}_{sc}$  and normally is zero.

There are ways to do emittance compensation to handle  $\mathcal{E}_{RF}$  and  $\mathcal{E}_{sc}$  {B. Carlsten, NIM A285, 313 (1989)}, so in principle, the only limitation left is the thermal emittance  $\mathcal{E}_{thermal}$ .

# SCHOTTKY-ENABLED PHOTOEMISSION 3 – Thermal Emittance

$$\varepsilon_{thermal} = \frac{1}{m_0 c} \sqrt{\langle x^2 \rangle \langle p_x^2 \rangle - \langle x \cdot p_x \rangle^2}$$

At the cathode  $\langle x \cdot p_x \rangle = 0$

Therefore, 
$$\varepsilon_{thermal,rms} = x_{rms} \frac{p_{rms}}{m_0 c} = x_{rms} \frac{\sqrt{2m_0 E_{kin}}}{m_0 c}$$

Minimizing  $E_{kin}$  will minimize  $\varepsilon_{thermal}$ .

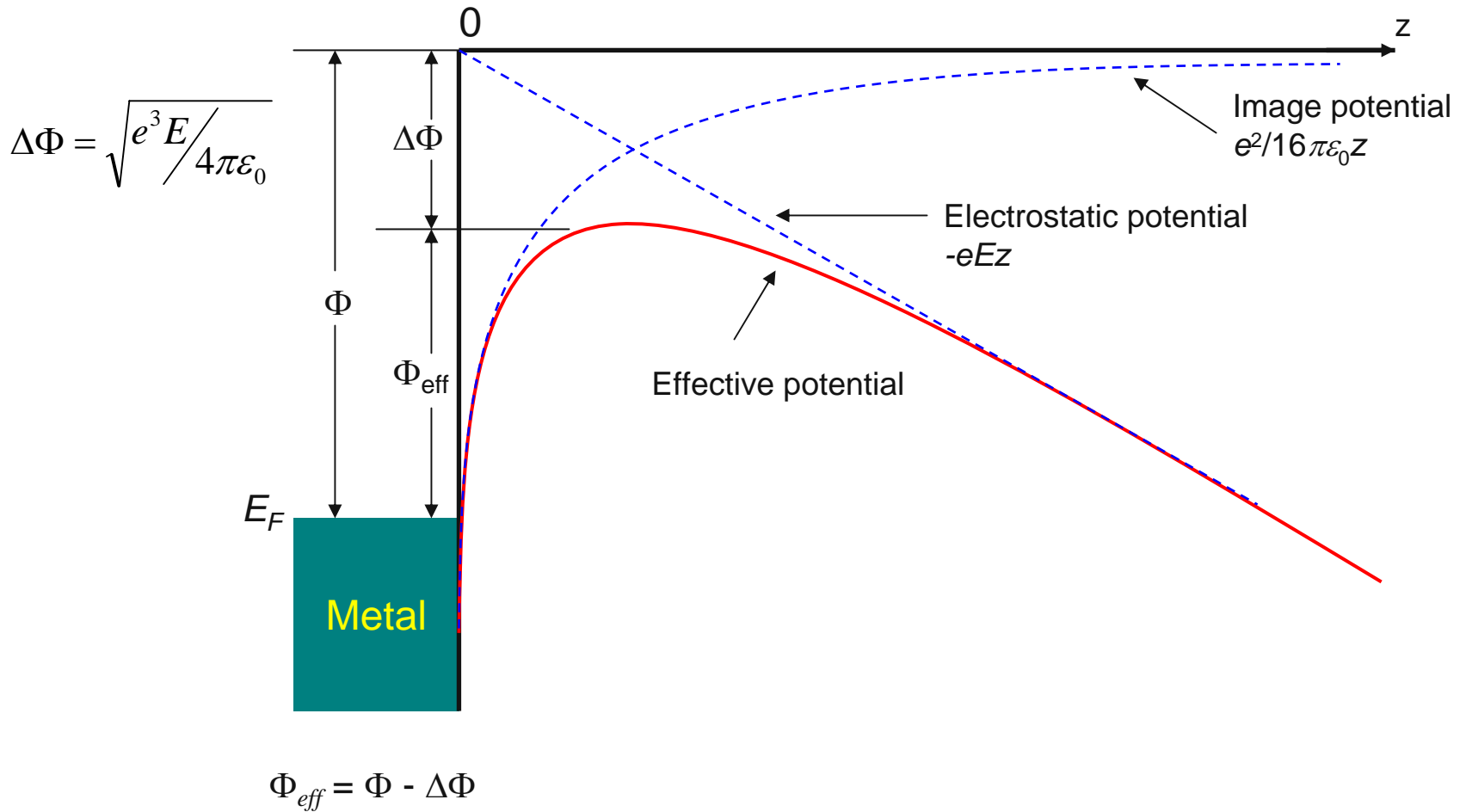
For a typical cathode:  $E_{kin} = h\nu - \Phi$

However, for a cathode in an electric field  $E$ : 
$$E_{kin} = h\nu - \underbrace{\Phi + \alpha \sqrt{\beta E(\phi)}}_{-\Phi_{eff}}$$

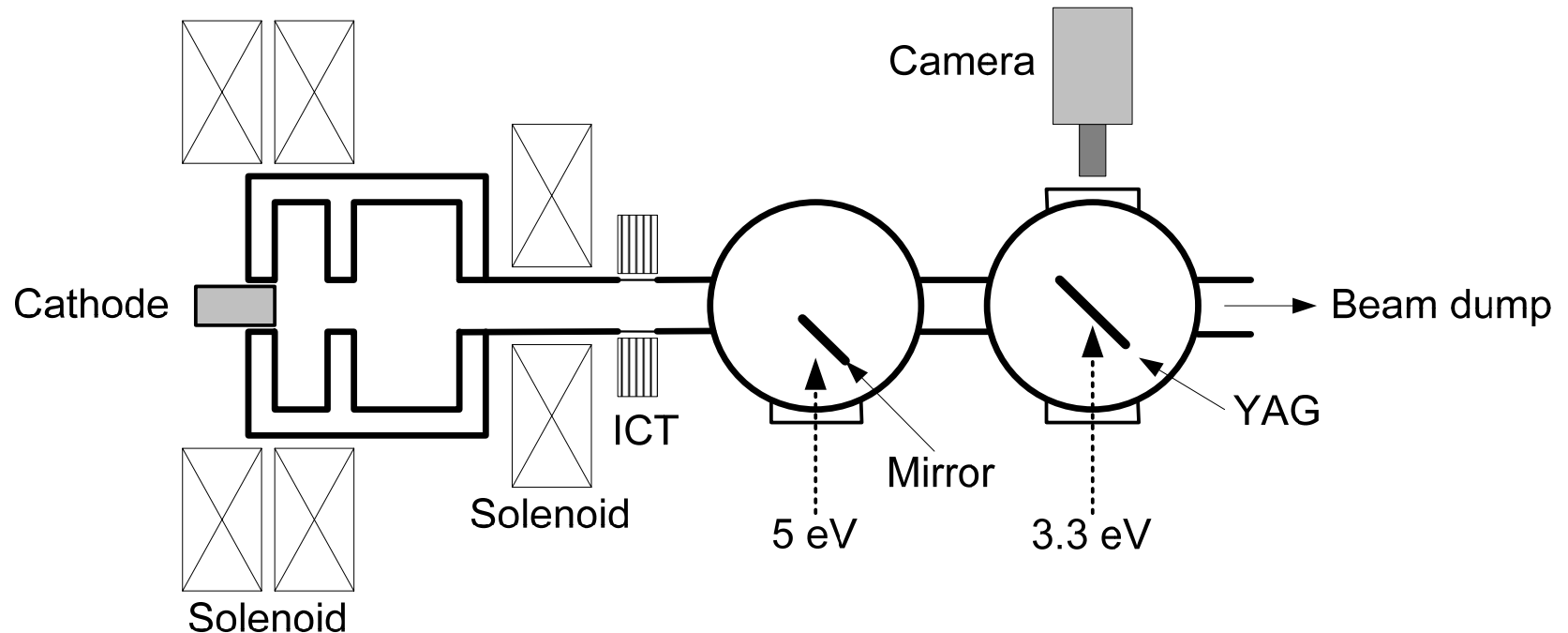
- where  $h\nu$  : photon energy
- $\Phi$  : material's bulk work function
- $\alpha$  : a constant
- $\beta$  : field enhancement factor
- $\phi$  : RF phase
- $E$  : Electric field magnitude

Our scheme is to use  $h\nu < \Phi$ , and then employ the Schottky effect to lower the effective work function  $\Phi_{eff}$ , where  $\Phi_{eff} = \Phi - \alpha \sqrt{\beta E(\theta)}$

# SCHOTTKY-ENABLED PHOTOEMISSION 4 – The Schottky Effect



# SCHOTTKY-ENABLED PHOTOEMISSION 5 – Schematic of Beamline

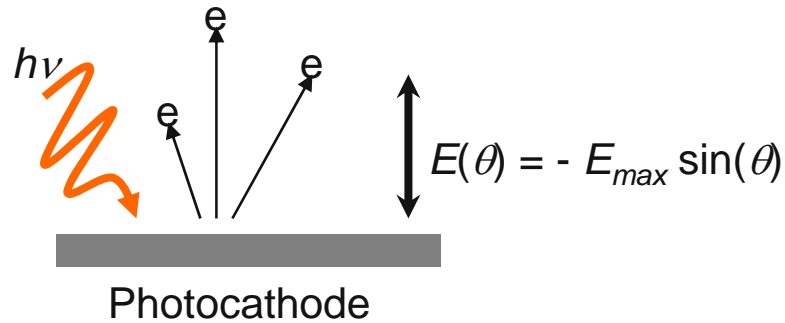


Light source: Frequency-doubled Ti:Sapphire laser 372 nm (3.3 eV), 1 – 4 mJ, 8ps.

Photocathode: Mg,  $\Phi = 3.6$  eV.

Example of Schottky effect on the cathode: at  $E(\theta) = 60$  MV/m,  $\Delta\Phi \sim 0.3$  eV

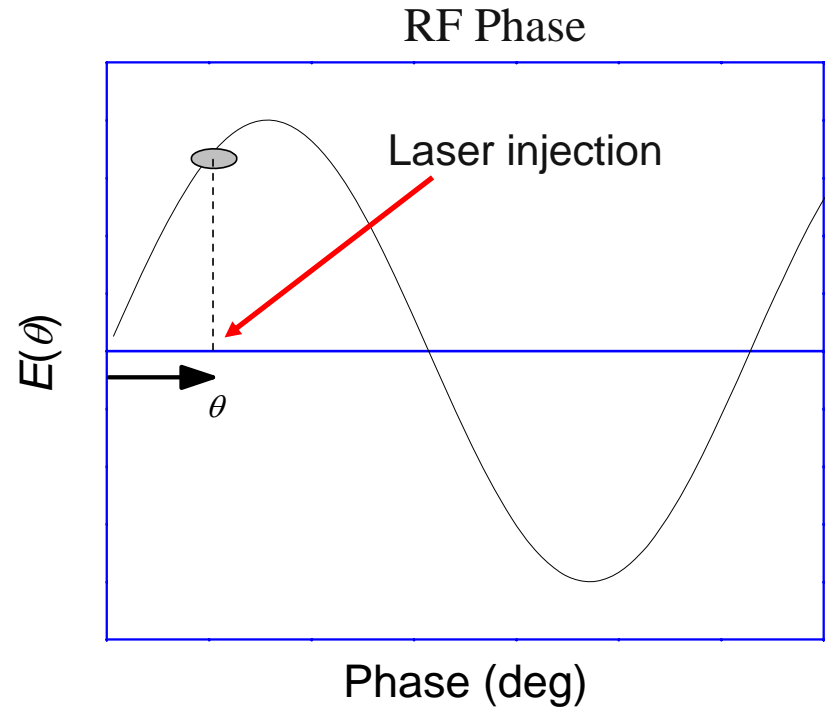
# SCHOTTKY-ENABLED PHOTOEMISSION 6 - RF Scans



RF frequency = 1.3 GHz (Period ~ 770 ps)

Laser pulse length = 6 – 8 ps

Metallic photocathode response time ~ fs

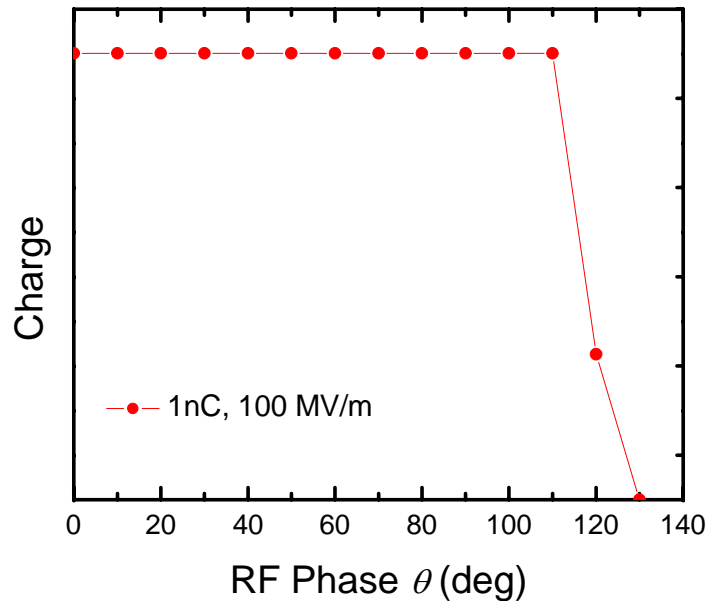


We can safely assume that all the photoelectrons emitted in each pulse see the same  $E$ -field strength



# SCHOTTKY-ENABLED PHOTOEMISSION 7 - Charge Obtained From Typical RF Scans

Theoretical RF Scan

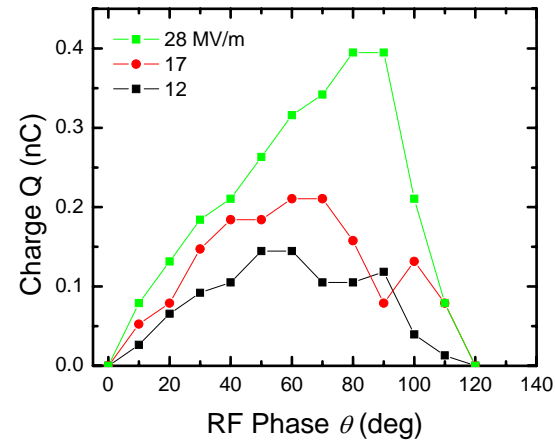


Theoretical result from PARMELLA simulation of our RF photoinjector (H. Wang)

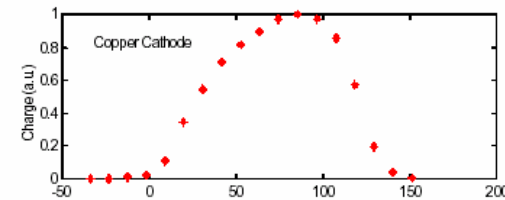
We see the “expected” flat-top profile

Full range of charge detected ~ 130 degrees

Experimental RF Scan



Our scans



X.J. Wang *et al.*  
Proc. 1998 LINAC

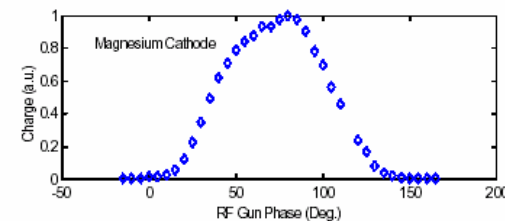
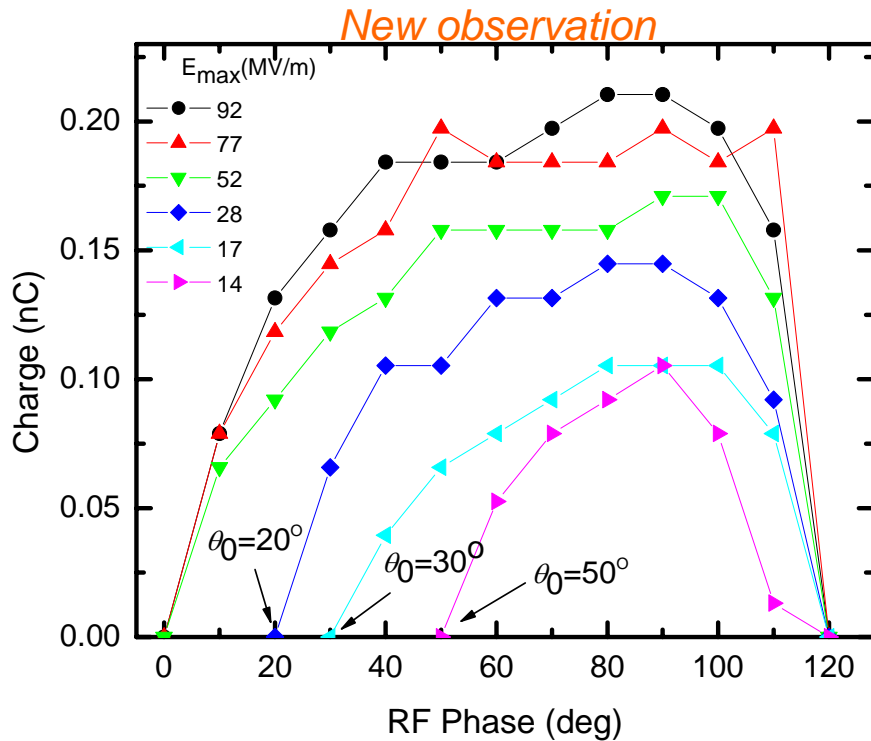


Figure 3: Photoelectron charge as function of RF gun phase for different cathode materials.

# SCHOTTKY-ENABLED PHOTOEMISSION 8 – Experimental Result 1: RF Phase Scans

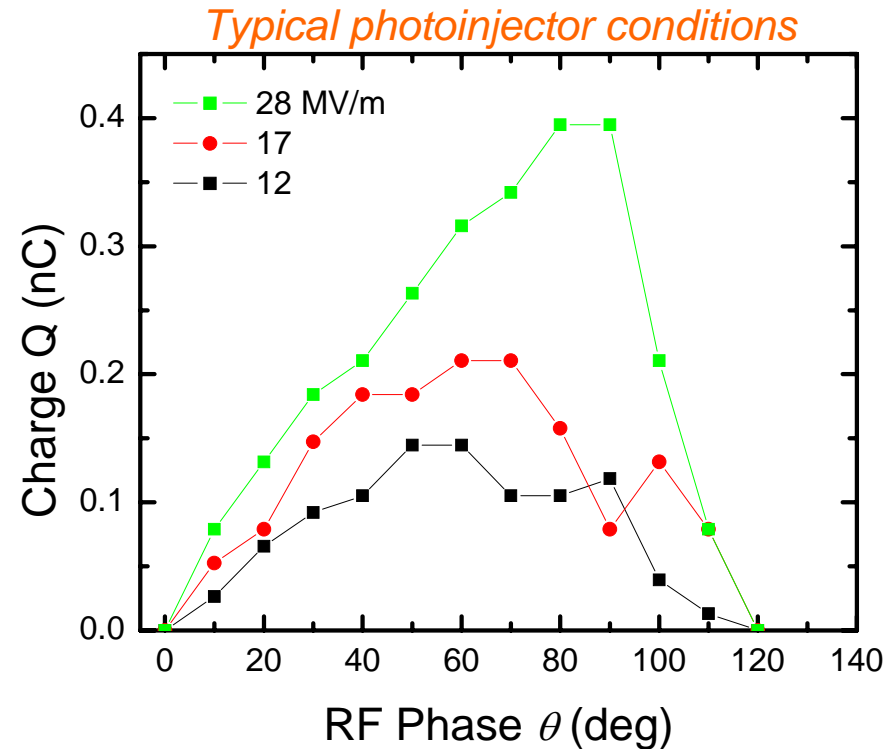
An RF phase scan allows us to impose different electric field magnitude on the cathode at the instant that a laser pulse impinges on the surface, i.e.  $E(\theta) = E_{max} \sin(\theta)$ .



$h\nu = 3.3 \text{ eV}; \Phi = 3.6 \text{ eV}$

Laser beam diameter = 2 cm ( $0.35 \text{ mJ/cm}^2$ )

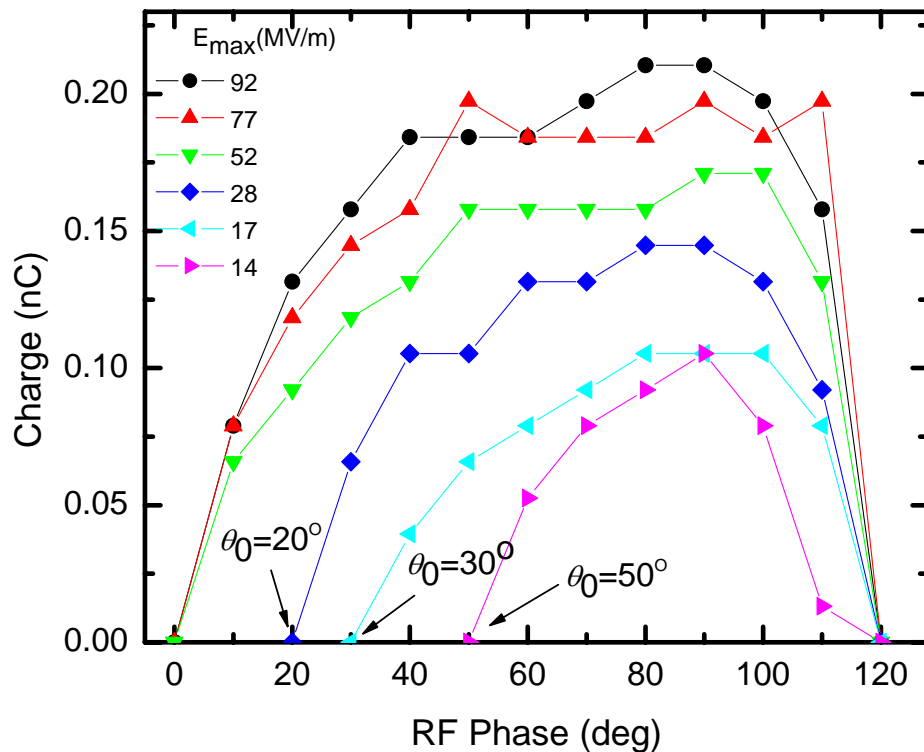
A noticeable shift of the onset of photoelectron production with decreasing RF power.



$h\nu = 5 \text{ eV}, \Phi = 3.6 \text{ eV}$

No change in the phase range over all RF power.

# SCHOTTKY-ENABLED PHOTOEMISSION 9 – Determination of Field-Enhancement Factor



$$h\nu = 3.3 \text{ eV}; \Phi = 3.6 \text{ eV}$$

$$Q \propto \left[ h\nu - \Phi + \alpha \sqrt{\beta E(\theta)} \right]^2$$

$$E(\theta) = E_{\max} \sin(\theta)$$

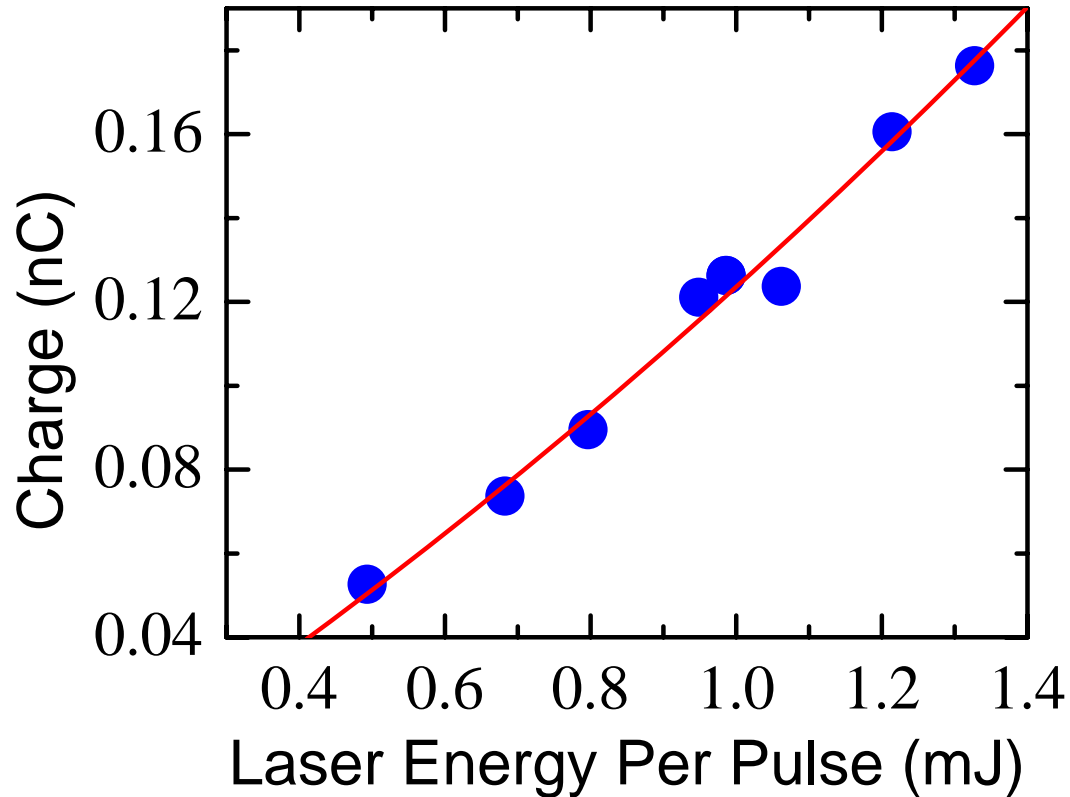
$$\alpha = \sqrt{\frac{e}{4\pi\epsilon_0}}$$

At threshold,  $Q = 0$ . This allows us to make a reasonable estimate of the maximum  $\beta$ .

$\theta_0$ (deg)	$E_{\max}$ (MV/m)	$E_0 = E_{\max} \sin(\theta_0)$ (MV/m)	$\beta$
20	28	9.2	6.8
30	17	8.5	7.3
50	14	11	5.8

This is a *new* and viable technique to realistically determine the field enhancement factor of the cathode in a photoinjector

# SCHOTTKY-ENABLED PHOTOEMISSION 10 - Experimental Result 2 : Intensity Dependence



Parameters:

$h\nu = 3.3 \text{ eV}$

$\Phi = 3.6 \text{ eV}$

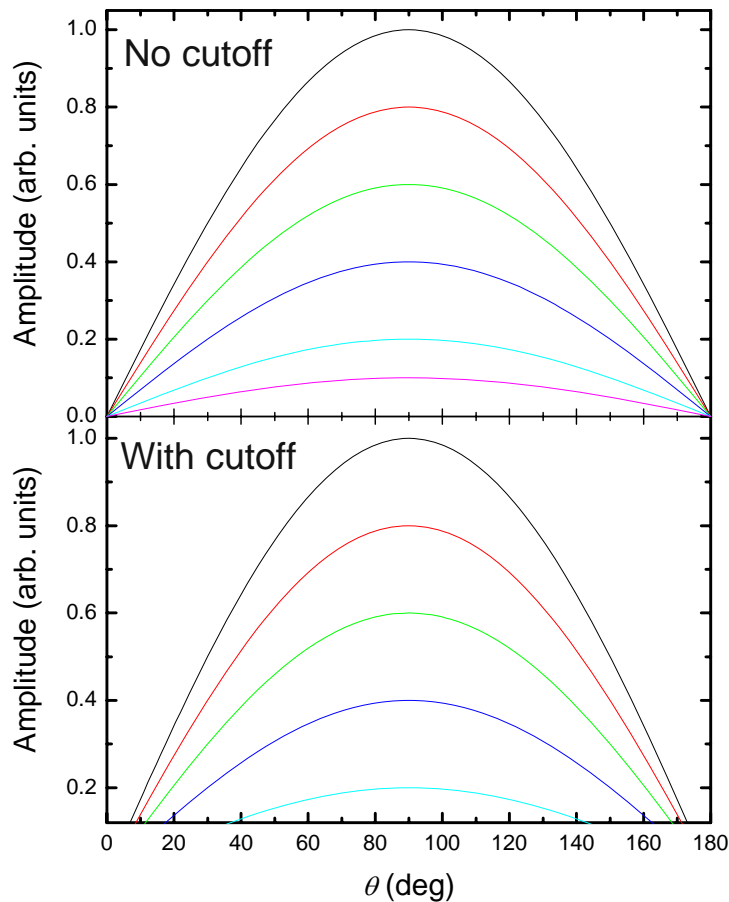
E field on cathode: 80 MV/m

Laser spot diameter: 2 cm

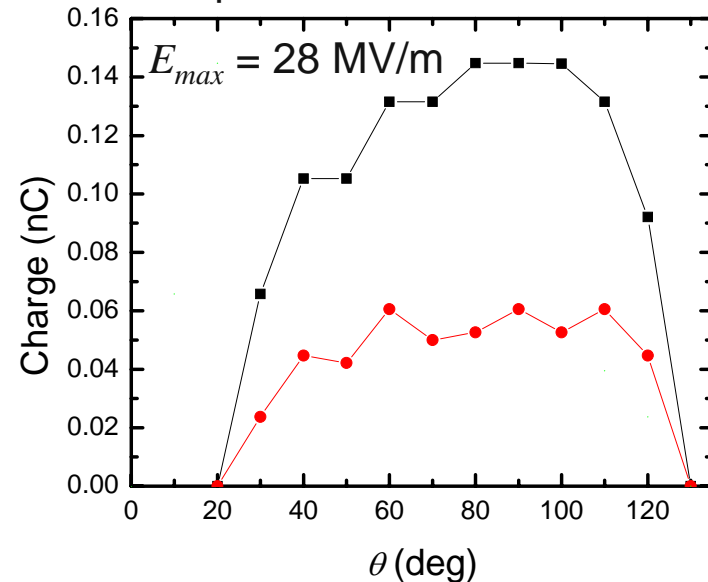
As we increase the laser intensity, we detect more charge. We *definitely* are detecting photoelectrons and not dark currents!

# SCHOTTKY-ENABLED PHOTOEMISSION 11- Experimental Results 3 : Detection Threshold?

Simulated Detection Threshold  
Using A Sine Function



Experimental Observation



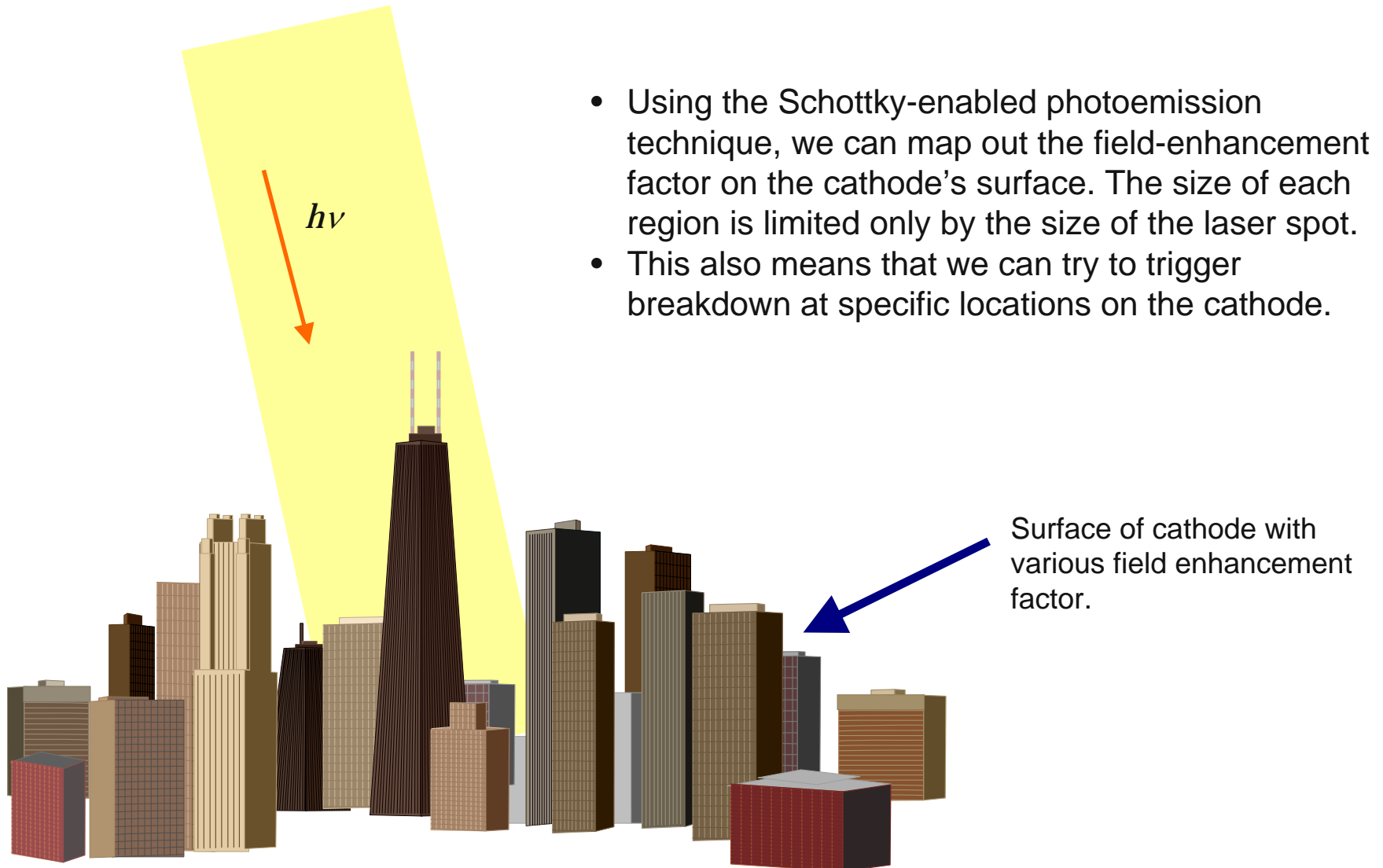
Two different scans with different amount of charge produced, but with the same RF amplitude, show the same phase angle for the photoemission threshold.

The shift in the photoemission threshold is **not** due to the detection threshold.

# HIGH GRADIENT/BREAKDOWN STUDIES 1

- Several different mechanisms have been proposed that triggers a breakdown event in high-gradient environment;
- All of them start with regions on the surface with high field-enhancement factor;
- Can we address/answer some of the nagging issues surrounding the breakdown mechanism?
- We would like to (i) map out the field-enhancement factor on the surface of a cathode, (ii) map out the dark current produced by the cathode, and (iii) try to trigger a breakdown event at a particular location using a combination of high fields and high-power laser.

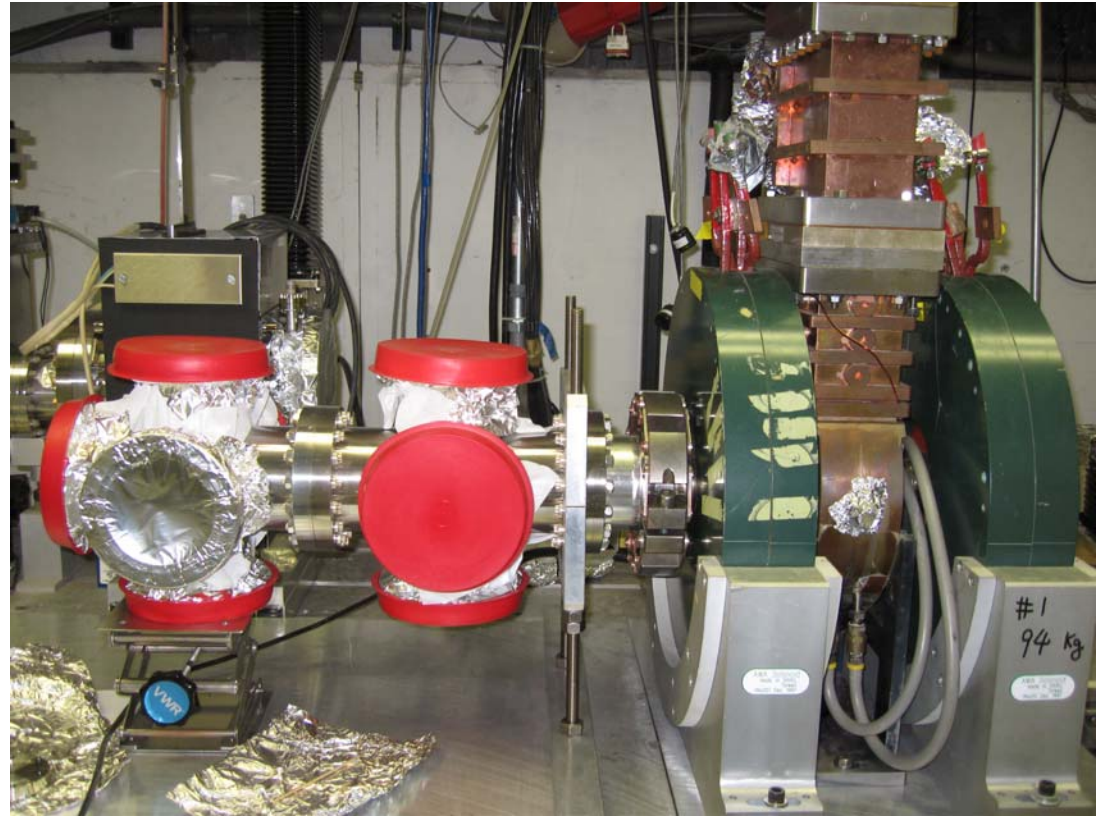
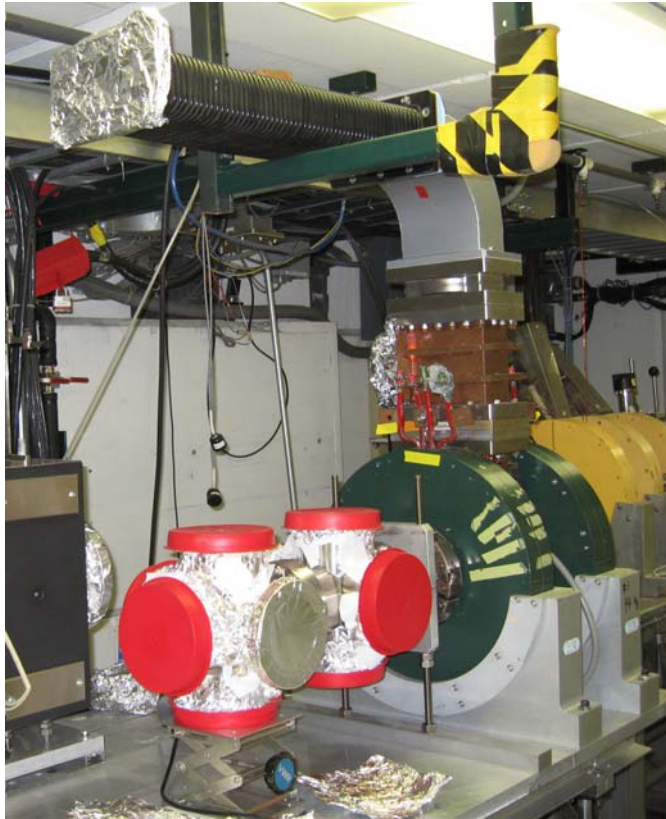
# HIGH GRADIENT/BREAKDOWN STUDIES 2 – Mapping Out The Field-Enhancement Factor





# HIGH GRADIENT/BREAKDOWN STUDIES 3 – Dedicated Facility

- ½ cell gun, Maximum gradient ~120 MV/m
- Diagnostics to be installed: ICT, Faraday cup, gated camera, etc.



# SUMMARY

- AWA needs high QE photocathode. Cs<sub>2</sub>Te seems to be the best candidate at the moment;
- The Schottky-enabled photoemission technique can, in principle, produce electron beam with low intrinsic emittance;
- The same technique can realistically determine the field enhancement factor of a cathode's surface *in situ*, independent of the Fowler-Nordheim model;
- The ability to determine the local field enhancement factor is the starting point for the high-gradient/breakdown studies.